



#### 60V 175°C P-CHANNEL ENHANCEMENT MODE MOSFET

### **Product Summary**

V <sub>(BR)DSS</sub>	R <sub>DS(ON)</sub> Max	I <sub>D</sub> Max T <sub>C</sub> = +25°C
001/	33mΩ @ V <sub>GS</sub> = -10V	-35A
-60V	40mΩ @ V <sub>GS</sub> = -4.5V	-32A

### Description

This MOSFET has been designed to meet the stringent requirements of Automotive applications.

# **Applications**

It is qualified to AECQ101, supported by a PPAP and is ideal for use in:

- Engine Management Systems
- Body Control Electronics
- DCDC Converters



Top View

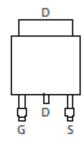
#### Features

- Rated to +175°C Ideal for High Ambient Temperature Environments
- 100% Unclamped Inductive Switching Ensures More Reliable and Robust End Application
- Low On-Resistance
- Low Input Capacitance
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

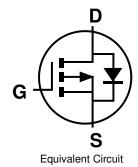
# Mechanical Data

- Case: TO252 (DPAK)
- Case Material: Molded Plastic, "Green" Molding Compound.
- UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Weight: 0.33 grams (Approximate)

#### TO252 (DPAK)



Pin Out Top View



Ordering Information (Note 4)

Part Number	Case	Packaging
DMPH6023SK3-13	TO252 (DPAK)	2,500/Tape & Reel

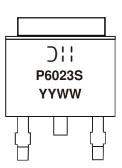
EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.
 See http://www.diodes.com/quality/lead\_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. For packaging details, go to our website at http://www.diodes.com/products/packages.html

### **Marking Information**

Notes:



):: =Manufacturer's Marking
P6023S = Product Type Marking Code
YYWW = Date Code Marking
YY = Last Digit of Year (ex: 15 = 2015)
WW = Week Code (01 to 53)



# Maximum Ratings (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Units		
Drain-Source Voltage	V <sub>DSS</sub>	-60	V		
Gate-Source Voltage			V <sub>GSS</sub>	±20	V
	Steady State	$T_{C} = +25^{\circ}C$ $T_{C} = +100^{\circ}C$	ID	-35 -27	A
Continuous Drain Current (Note 6) $V_{GS} = -10V$	Steady State	$T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$	ID	-7.3 -6.1	А
Pulsed Drain Current (380µs pulse, duty cycle = 1%)			I <sub>DM</sub>	-60	A
Maximum Continuous Body Diode Forward Current (Note 6)			Is	-2.2	A
Avalanche Current (Note 7) L = 0.1mH			IAS	-35	A
Avalanche Energy (Note 7) L = 0.1mH			E <sub>AS</sub>	60	mJ

# **Thermal Characteristics**

Characteristic	Symbol	Value	Units	
Total Power Dissipation (Note 5)		PD	2.0	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	R <sub>0JA</sub>	80	°C/W
Total Power Dissipation (Note 6)		PD	3.2	W
ermal Resistance, Junction to Ambient (Note 6) Steady State		R <sub>0JA</sub>	41	°C/W
Thermal Resistance, Junction to Case		Rejc	1.6	-C/W
Operating and Storage Temperature Range		T <sub>J,</sub> T <sub>STG</sub>	-55 to +175	°C

# Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

h							
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 8)	-	-			-	-	
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	-60	—		V	$V_{GS} = 0V, I_D = -250 \mu A$	
Zero Gate Voltage Drain Current $T_J = +25^{\circ}C$	I <sub>DSS</sub>	—		-1	μA	$V_{DS} = -60V, V_{GS} = 0V$	
Gate-Source Leakage	IGSS		—	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 8)							
Gate Threshold Voltage	V <sub>GS(th)</sub>	-1.0	—	-3.0	V	$V_{DS} = V_{GS}$ , $I_D = -250 \mu A$	
Static Drain-Source On-Resistance	Passa	_	_	33	mΩ	$V_{GS} = -10V, I_D = -10A$	
	R <sub>DS(ON)</sub>		—	40	11152	$V_{GS} = -4.5V, I_D = -8A$	
Diode Forward Voltage	V <sub>SD</sub>		-0.7	-1.2	V	$V_{GS} = 0V, I_{S} = -1A$	
DYNAMIC CHARACTERISTICS (Note 9)							
Input Capacitance	Ciss		2,569		pF		
Output Capacitance	Coss		179		pF	$V_{DS} = -30V, V_{GS} = 0V,$ f = 1.0MHz	
Reverse Transfer Capacitance	C <sub>rss</sub>		143		pF		
Gate Resistance	Rg		5	—	Ω	$V_{DS} = 0V$ , $V_{GS} = 0V$ , $f = 1MHz$	
Total Gate Charge (V <sub>GS</sub> = -4.5V)	Qg		26.5		nC		
Total Gate Charge (V <sub>GS</sub> = -10V)	Qg		53.1	—	nC	Vps = -30V. lp = -5A	
Gate-Source Charge	Q <sub>gs</sub>	_	7.1	_	nC	$v_{DS} = -30v$ , $I_D = -3A$	
Gate-Drain Charge	Q <sub>gd</sub>	_	12.6	_	nC	7	
Turn-On Delay Time	t <sub>D(on)</sub>	_	6	_	nS		
Turn-On Rise Time	tr		7.1	_	nS		
Turn-Off Delay Time	t <sub>D(off)</sub>		110	_	nS	$R_G = 3\Omega, I_D = -5A$	
Turn-Off Fall Time	tf		62		nS	7	
Body Diode Reverse Recovery Time	t <sub>rr</sub>	—	20		nS		
Body Diode Reverse Recovery Charge	Q <sub>rr</sub>	—	14	—	nC	I <sub>F</sub> = -5A, di/dt = 100A/μs	

5. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout, see http://www.diodes.com/datasheets/ap02001.pdf Notes: for the latest version.

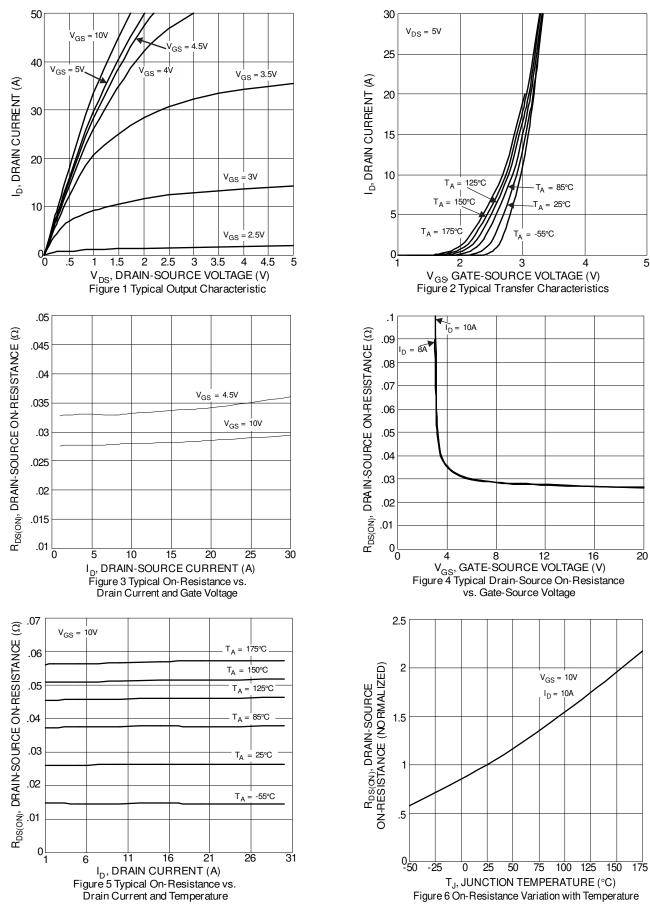
6. Device mounted on FR-4 substrate PC board, 2oz copper, with 1-inch square copper plate.

7. IAS and EAS rating are based on low frequency and duty cycles to keep  $T_J = +25^{\circ}C$ 8. Short duration pulse test used to minimize self-heating effect.

9. Guaranteed by design. Not subject to product testing.

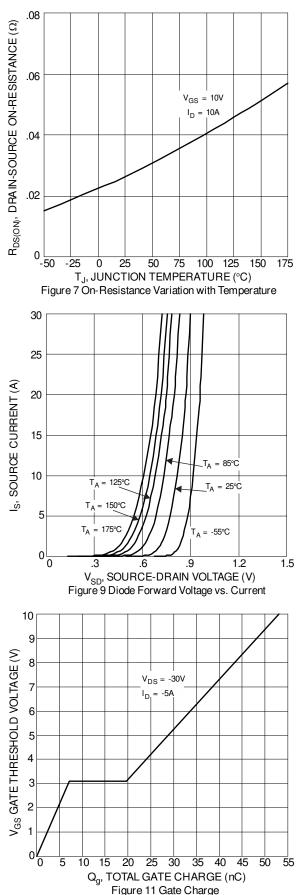


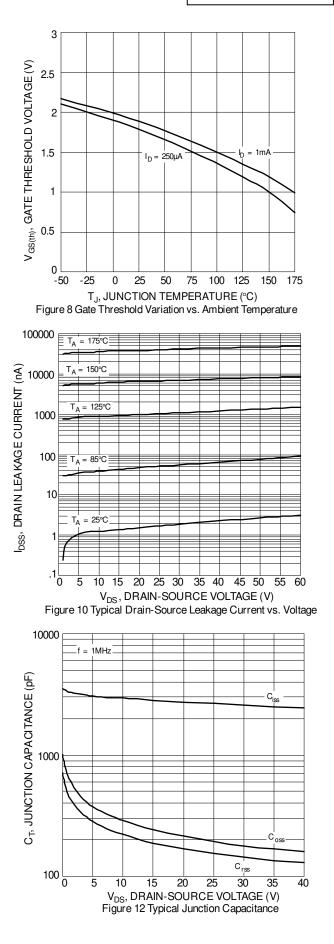
## **DMPH6023SK3**



# **DMPH6023SK3**

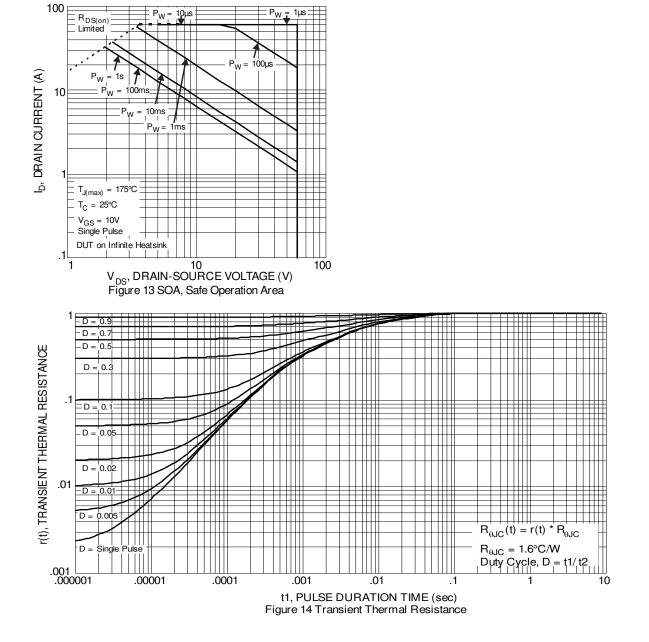








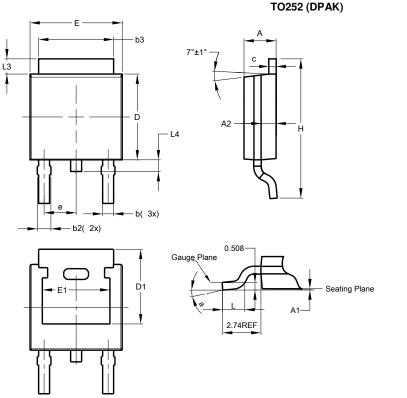






# **Package Outline Dimensions**

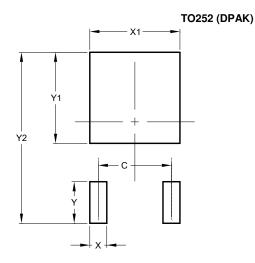
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.



TO252 (DPAK)						
Dim	Min	Max	Тур			
Α	2.19	2.39	2.29			
<b>A1</b>	0.00	0.13	0.08			
A2	0.97	1.17	1.07			
q	0.64	0.88	0.783			
b2	0.76	1.14	0.95			
b3	5.21	5.46	5.33			
С	0.45	0.58	0.531			
D	6.00	6.20	6.10			
D1	5.21	-	_			
е	_	_	2.286			
Е	6.45	6.70	6.58			
E1	4.32	_	—			
Η	9.40	10.41	9.91			
L	1.40	1.78	1.59			
L3	0.88	1.27	1.08			
L4	0.64	1.02	0.83			
а	0°	10°	—			
All Dimensions in mm						

# **Suggested Pad Layout**

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)			
С	4.572			
Х	1.060			
X1	5.632			
Y	2.600			
Y1	5.700			
Y2	10.700			



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